METHOD FOR DIVIDING SEMICONDUCTOR WAFER ALONG STREETS

Abstract of the Disclosure

A method for dividing a semiconductor wafer along a plurality of streets, the semiconductor wafer having a face on which a plurality of rectangular regions are defined by the streets arranged in a lattice pattern, and a semiconductor device is formed in each of the rectangular regions. This method comprises a protective member coating step of coating the face of the semiconductor wafer with a protective member, a resist film coating step of coating the back of the semiconductor wafer, except sites corresponding to the streets, with a resist film, and a plasma etching step of applying plasma etching to the back of the semiconductor wafer to divide the semiconductor wafer along the streets.

Figure 6